MGFC39V3742A

3.7 ~ 4.2GHz BAND 8W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC39V3742A is an internally impedance-matched GaAs power FET especially designed for use in 3.7 ~ 4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation
Internally matched to 50(ohm) system
High output power
P1dB = 8W (TYP.) @ f=3.7~4.2GHz
High power gain
GLP = 12 dB (TYP.) @ f=3.7~4.2GHz
High power added efficiency
P.A.E. = 31 % (TYP.) @ f=3.7~4.2GHz
Low distortion [item -51]
IM3= -45 dBc(TYP.) @ Po=28dBm S.C.L.

APPLICATION

item 01: 3.7~4.2 GHz band power amplifier

item 51: 3.7~4.2 GHz band digital radio communication

QUALITY GRADE

IG

RECOMMENDED BIAS CONDITIONS

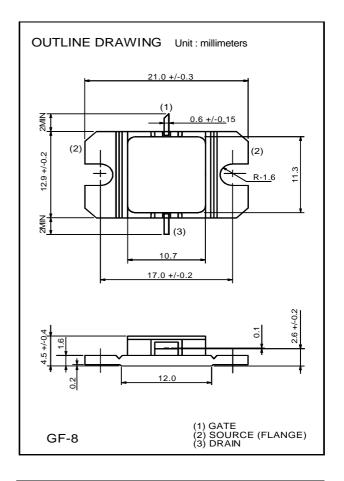
VDS = 10(V)ID = 2.4 (A)

Rg = 50(ohm) Refer to Bias Procedure

ABSOLUTE MAXIMUM RATINGS (Ta=25 deg.C)

Symbol	Parameter	Ratings	Unit	
VGDO	Gate to drain voltage -15		V	
VGSO	Gate to source voltage -15		V	
ID	Drain current	7.5	Α	
IGR	Reverse gate current	-20	mA	
IGF	Forward gate current	42	mA	
PT	Total power dissipation *1	42.8	W	
Tch	Channel temperature	175	deg.C	
Tstg	Storage temperature	-65 / +175	deg.C	

^{*1 :} Tc=25 deg.C



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ELECTRICAL CHARACTERISTICS (Ta=25 deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
Symbol	Faiailletei	rest conditions	Min.	Тур.	Max.	Offic
IDSS	Saturated drain current	VDS=3V, VGS=0V	1	-	7.5	Α
gm	Transconductance	VDS=3V, ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=20mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression		38	39.5	-	dBm
GLP	Linear power gain	VDS=10V, ID(RF off)=2.4A, f=3.7~4.2GHz	9	12	-	dB
ID	Drain current		-	-	3	Α
P.A.E.	Power added efficiency		-	31	-	%
IM3	3rd order IM distortion *1		-42	-45	-	dBc
Rth(ch-c)	Thermal resistance *2	Delta Vf method	-	-	3.5	deg.C/W

^{*1 :} item -51, 2 tone test, Po=28dBm Single Carrier Level, f=4.2GHz, Delta f=10MHz



^{*2 :} Channel to case

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